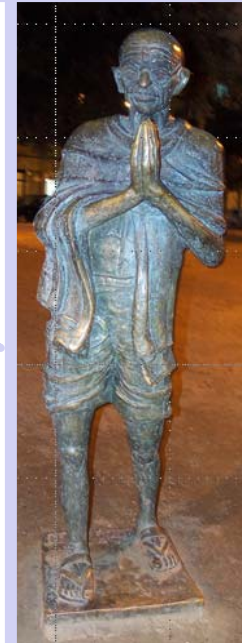


# Design Tools for Beyond CMOS

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# My View

1. Greatest new technologies find entirely new applications of their own.  
*NP complete, robust decision making in the midst of uncertainty in devices, information input, incomplete description of the problem.*
2. For new technologies, design systems are certainly very important, but robust design systems will nearly always be insufficient for the purpose of competing to an entrenched 50 year technology infrastructure. (bipolar, nmos, cmos, ...).  
*New technology in entrenched spaces finds an application – digital watch for CMOS – to slowly penetrate and evolve.*
3. But, it is possible to make reasonable judgment *when some characteristic is truly inappropriate for a replacement task.*
4. If we really want to have the freedom to explore architectures, new devices in some design context, functions, ..., *it must be open so different expertise can come together. This needs interfaces and all the necessary attributes specified in a defined format that are required by fiat. Robustness, variabilities, functional description, ... all need to be part of the framework's design and this is something those who give money can enforce.*

# Example: Characteristics Charge

Problem of today:

Variability(Control), Off-state current, Turn-on sharpness, Drive Current

Wires

Source Region    Gate All Around Region    Drain Region

$$\frac{1}{r} \frac{\partial}{\partial r} r \frac{\partial \psi}{\partial r} + \frac{\partial^2 \psi}{\partial y^2} = 0$$

Scaling:  $r' = \lambda r, y' = \lambda y$

$$\frac{1}{r'} \frac{\partial}{\partial r'} r' \frac{\partial \psi}{\partial r'} + \frac{\partial^2 \psi}{\partial y'^2} = 0$$

If aspect ratio retained (scaling), potential profile invariant

How small? Tunneling – off-state in traditional, on-state in tunnel FETs

$$I \propto T \approx \frac{\exp(-2\Gamma_{ba})}{\left[1 + \frac{1}{4} \exp(-2\Gamma_{ba})\right]^2} \approx \exp(-2\Gamma_{ba}) = \exp\left[-2 \int_a^b \gamma(y) dy\right]$$

$$\exp\left(-2 \int \sqrt{\frac{2m^*}{\hbar^2} [V(y) - E]} dy\right) \approx \exp\left[-2\sqrt{\frac{2m^*}{\hbar^2}} \left(\sqrt{V}L - \frac{EL}{2\sqrt{V}} + \dots\right)\right]$$

1<sup>st</sup> order term:

Current proportional to square root of potentials in barrier. Slow swing  
Variance inversely proportional to length scale – tunneling.

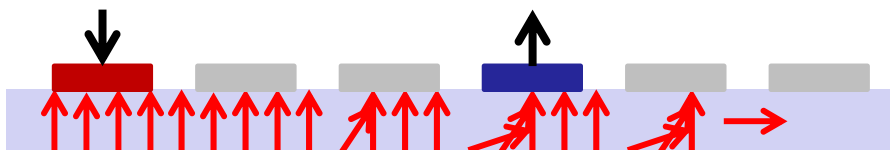
Problem is law of large numbers in its Poisson limit.

Problems of graphene, nanotubes, are much worse because of additional size, energy and its line width effects.

# Example: Characteristics

# Spin

Magnetization switching with spin current, spin qubits, ..., spin-torque flipping limits



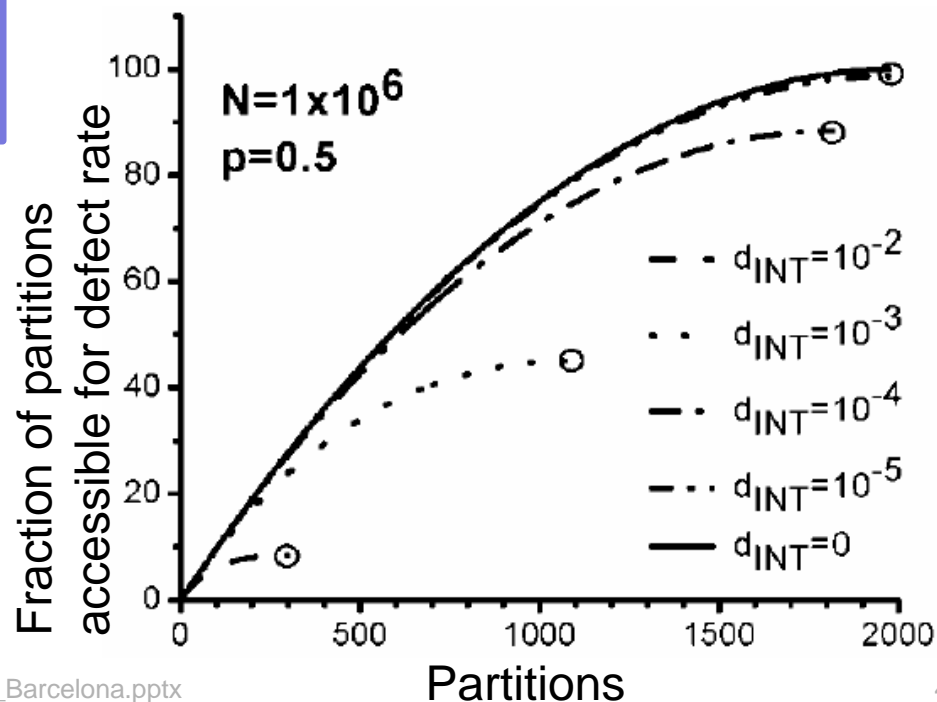
Spin transport, Signal loss  $\leftrightarrow$  failure rate

$$q = 1 - \exp\left(-\frac{\ell}{\lambda_c}\right)$$

for  $q = .001$   $\ell = 0.001\lambda_c$   
 if  $\lambda_c = 100 \mu m$ ,  $\Rightarrow \ell = 100 nm$

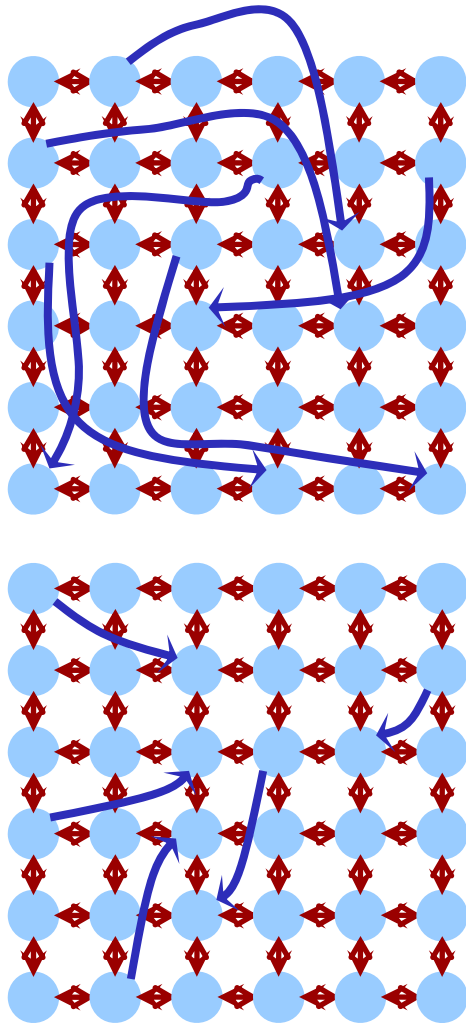
For normal distribution of errors,  
 fraction of usability.  
 This in turn raises power for error  
 correction, and devices that cannot  
 be used.

Signal recoverable up to  $q$  of  $\frac{1}{2}$ . If  
 $\lambda_c/2 = 50 \mu m$ , energy of  
 $\approx 1 V \times 10 \mu A = 10 \mu W$  needed  
 per recovery, or  $400 mW/cm^2$ + area.  
 I think these are quite optimistic  
 numbers.



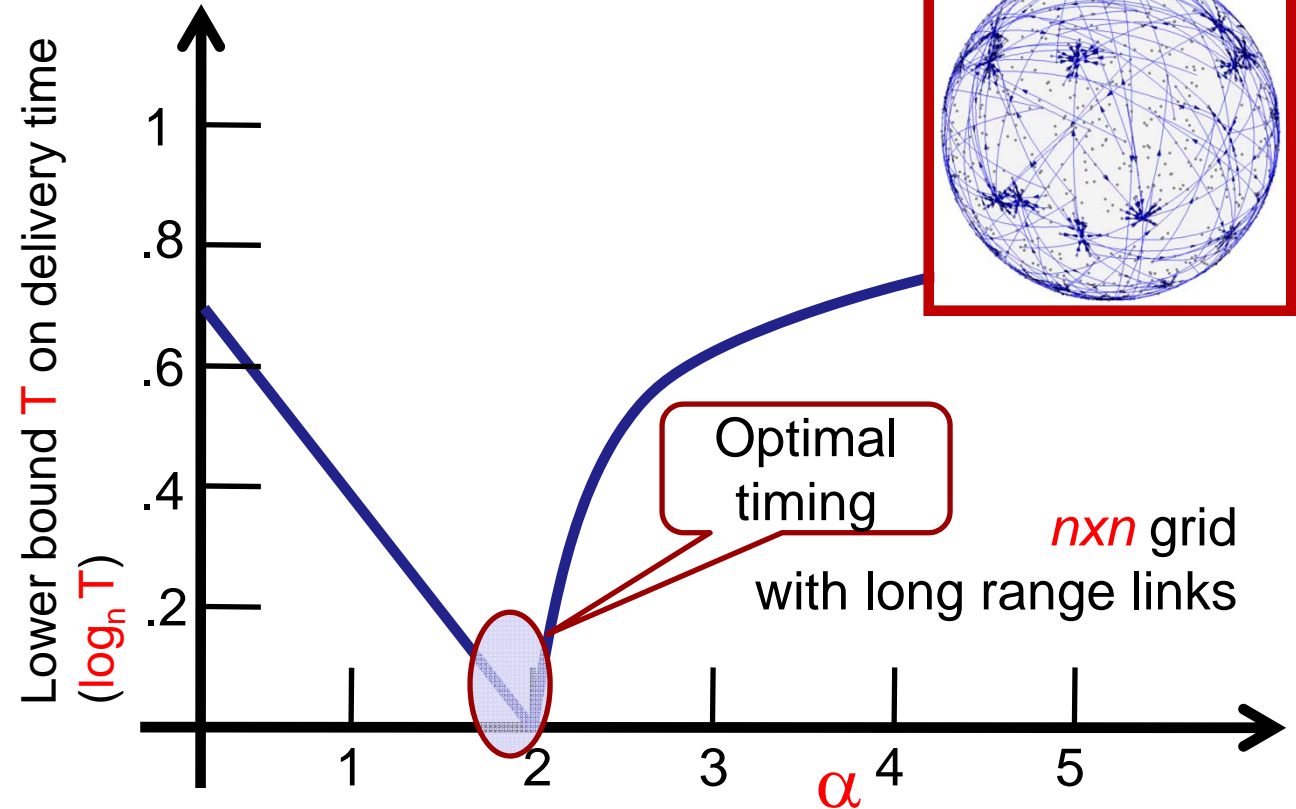
# An Important Issue We Forget: Networks – Timing in Large Integration

Small World Network: A class of networks with orderly local structure and small diameter  
Watts-Strogatz (1998)



Build a mixture of long range and short range for robustness

Long range percolation model: For each node  $v$ , add directed link to random node  $w$  with probability proportional to  $p(v,w)^{-\alpha}$  where  $p(v,w)$  is the lattice distance from  $v$  to  $w$ .



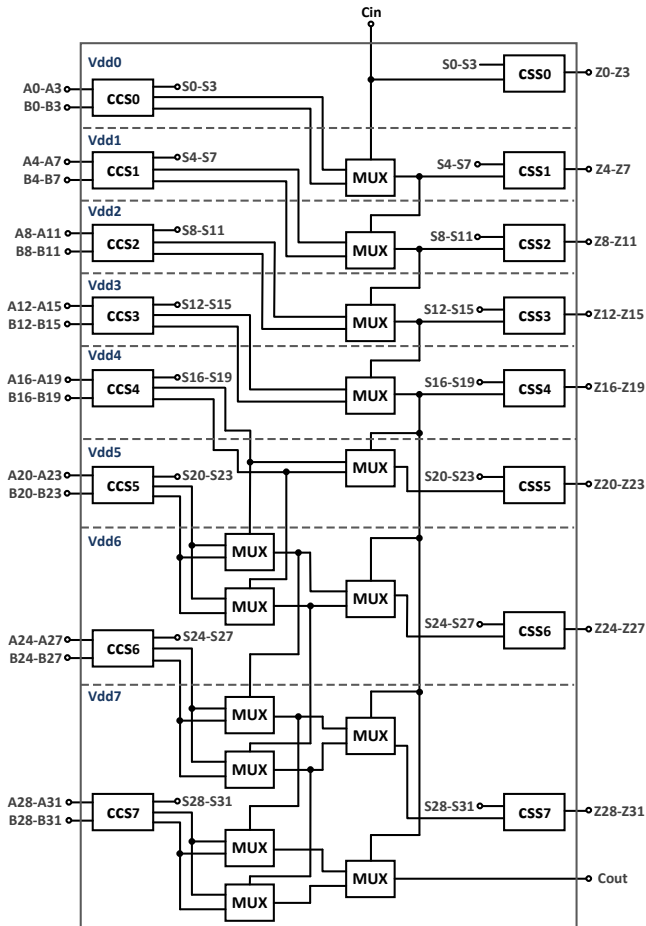
# *New Computing Models*

Learn to live with errors.

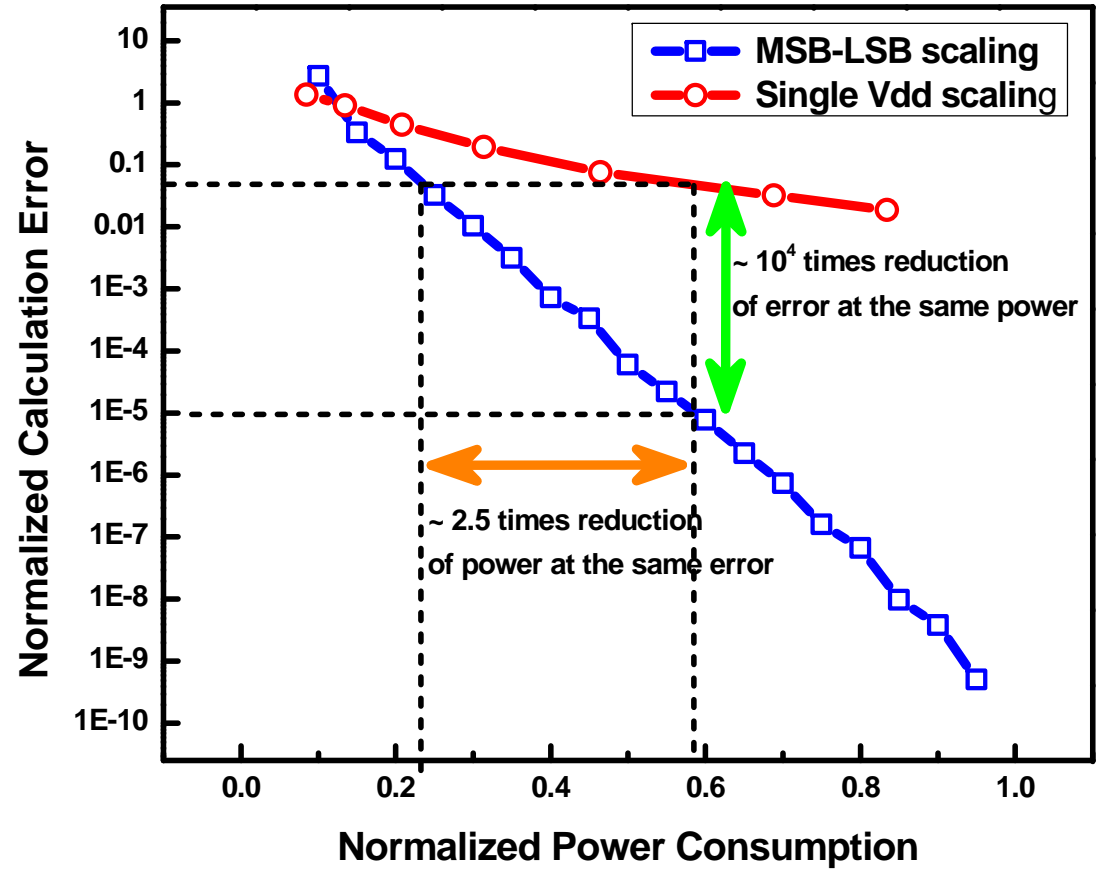
Indeed, take advantage of it to get robustness in presence of uncertainty from all the different sources.

# Inexact Addition

MSB-LSB weighted scaling of supply voltages for 32-bit CCS-CSS adders



Adder Block

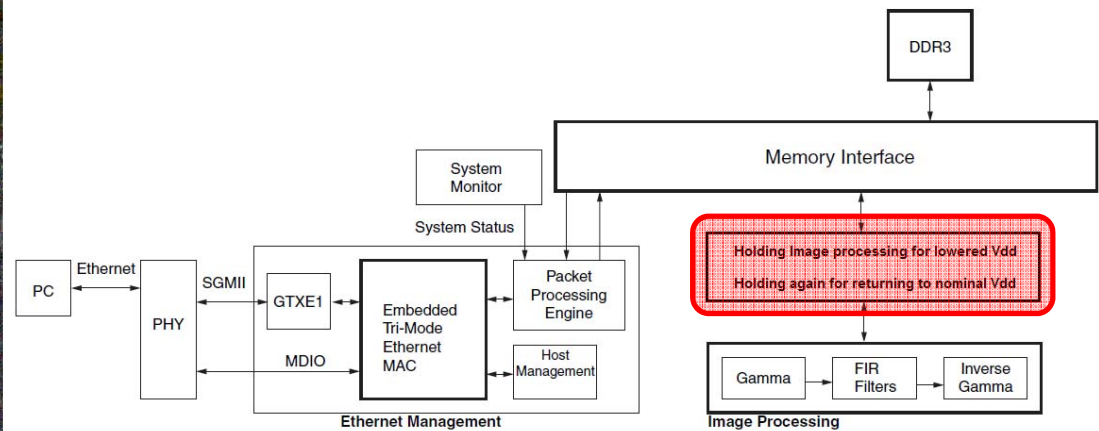


Kim & Tiwari, NanoAch ACM (2011)

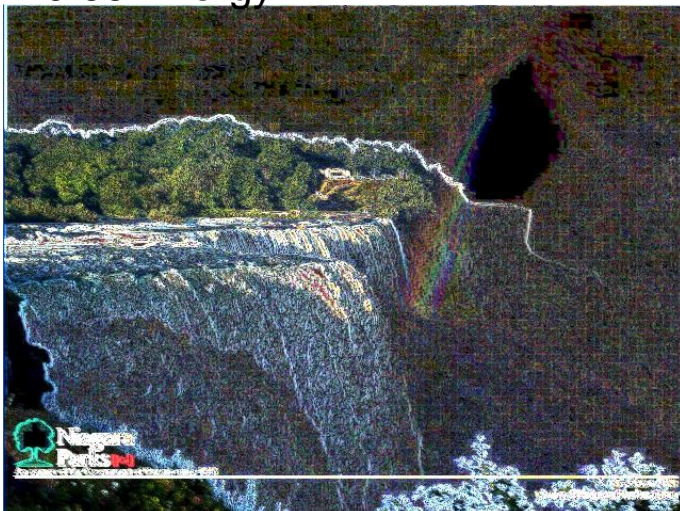
# Image Processing through Inexactness from DSP Lower Voltages

Kim & Tiwari (2011)

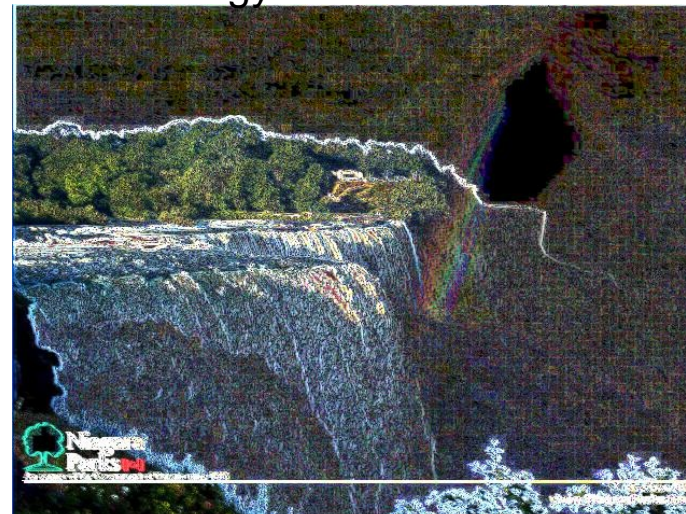
x0.52 Energy



x0.66 Energy



x1.0 Energy





# Bayesian Engines

Machine learning models – hidden Markov, neural nets, ... Bayesian/Belief networks

Such Bayesian probabilistic networks for AI, signal processing, data mining, .... in dedicated hardware.

Acyclic Graphs:

$$p(X_1, \dots, X_n) = \prod_{i=1}^n p[X_i | Parent_i]$$

Outgoing: **Sum-product normalized**  
Incoming: **Max-sum normalized**

Basic  
Computational  
Blocks



Dedicated evolving networked hardware using suitable electronic devices. High FI, High FO

Probabilistic gates of Inexact approaches

**This opens up thinking about new devices in an entirely new way.**

*Tiwari, Lin, Weijia, Palem, ...*